



Features

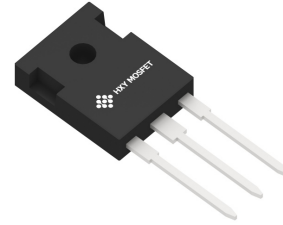
- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

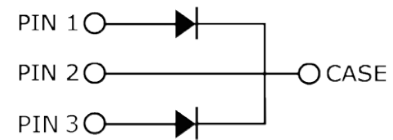
- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



TO-247



Part Number	Packag	Qty(PCS)
FFSH40120ADN-F085	TO-247	30

Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V _{RSM}	Surge Peak Reverse Voltage	1300	V		
V _R	DC Peak Reverse Voltage	1200	V		
I _F	Continuous Forward Current (Per Leg/Device)	56.5/113 27/54 20/40	A	T _C =25°C T _C =135°C T _C =150°C	Fig. 3
I _{FRM}	Repetitive Peak Forward Surge Current	91* 61*	A	T _C =25°C, t _p =10 ms, Half Sine Pulse T _C =110°C, t _p =10 ms, Half Sine Pulse	
I _{FSM}	Non-Repetitive Forward Surge Current	130* 110*	A	T _C =25°C, t _p =10 ms, Half Sine Pulse T _C =110°C, t _p =10 ms, Half Sine Pulse	Fig. 8
I _{F,Max}	Non-Repetitive Peak Forward Current	1150* 950*	A	T _C =25°C, t _p =10 ms, Pulse T _C =110°C, t _p =10 ms, Pulse	Fig. 8
P _{tot}	Power Dissipation (Per Leg/Device)	266/532 114/228	W	T _C =25°C T _C =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-960V	
∫i ² dt	i ² t value	84.5* 60.5*	A ² s	T _C =25°C, t _p =10 ms T _C =110°C, t _p =10 ms	
T _J	Operating Junction Range	-55 to +175	°C		
T _{stg}	Storage Temperature Range	-55 to +135	°C		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

* Per Leg, ** Per Device



Electrical Characteristics (Per Leg)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.2	1.8 3	V	$I_F = 20\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 20\text{ A}$ $T_J = 175^\circ\text{C}$	Fig. 1
I_R	Reverse Current	35 65	200 400	μA	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	Fig. 2
Q_C	Total Capacitive Charge	99		nC	$V_R = 800\text{ V}$, $I_F = 20\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	1500 93 67		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 800\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	Fig. 6
E_C	Capacitance Stored Energy	28		μJ	$V_R = 800\text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.29** 0.57*	$^\circ\text{C}/\text{W}$	Fig. 9

* Per Leg, ** Per Device

Typical Performance (Per Leg)

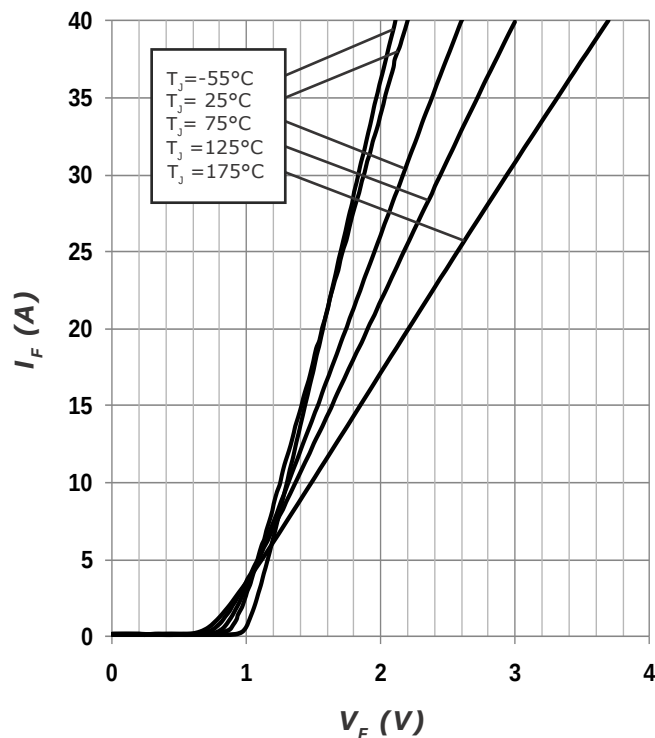


Figure 1. Forward Characteristics

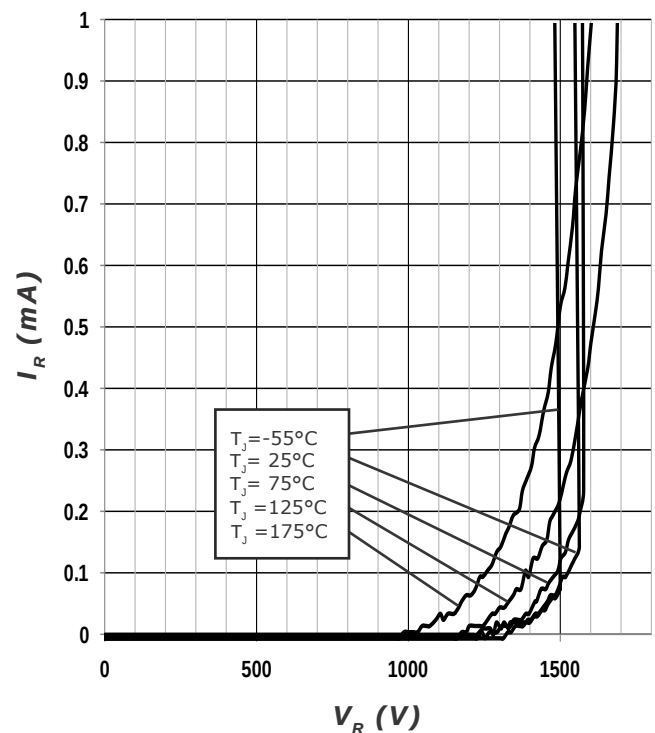


Figure 2. Reverse Characteristics



Typical Performance (Per Leg)

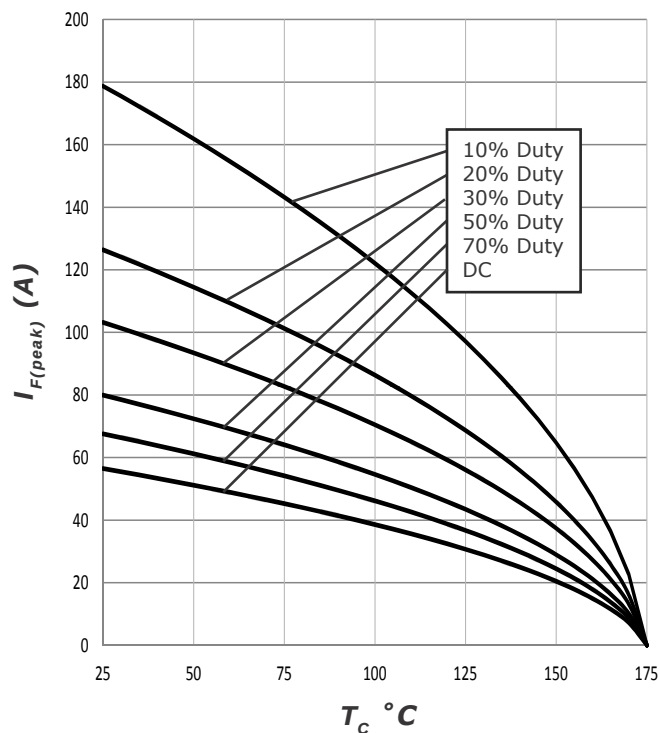


Figure 3. Current Derating

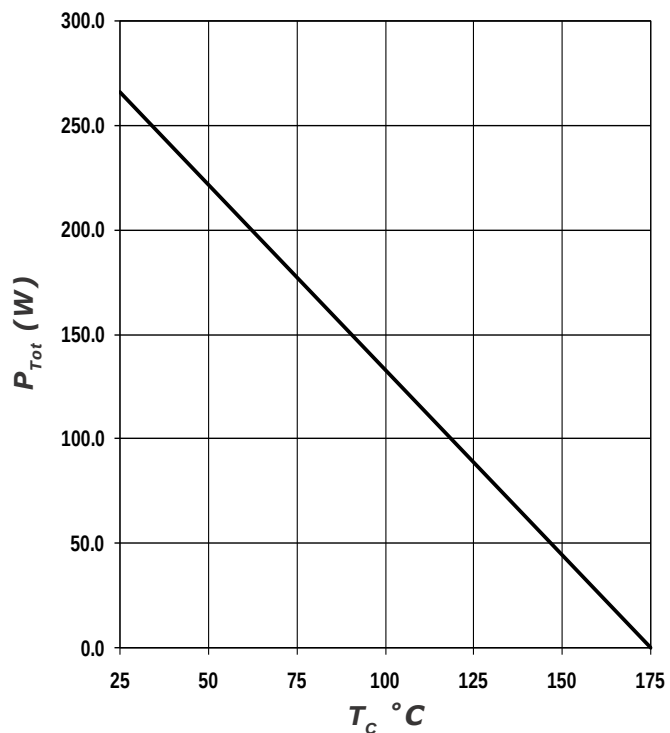


Figure 4. Power Derating

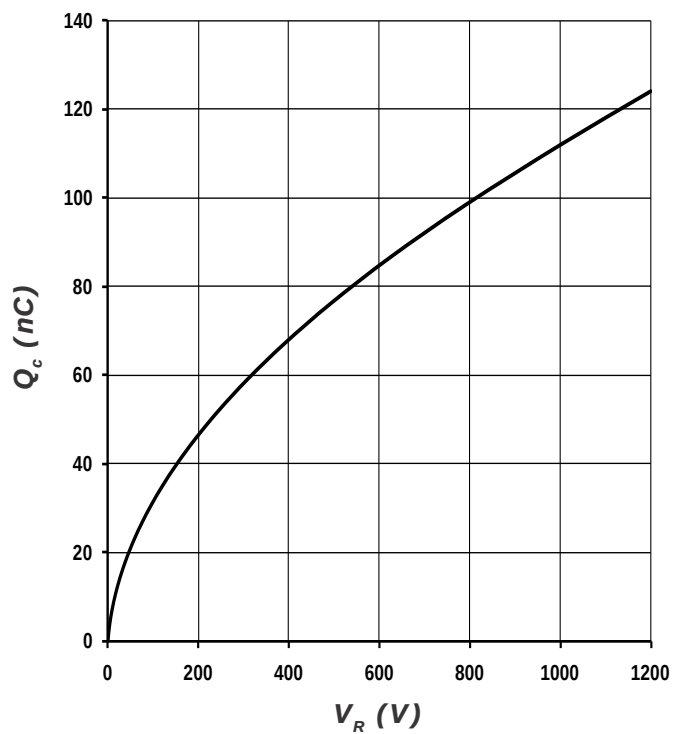


Figure 5. Recovery Charge vs. Reverse Voltage

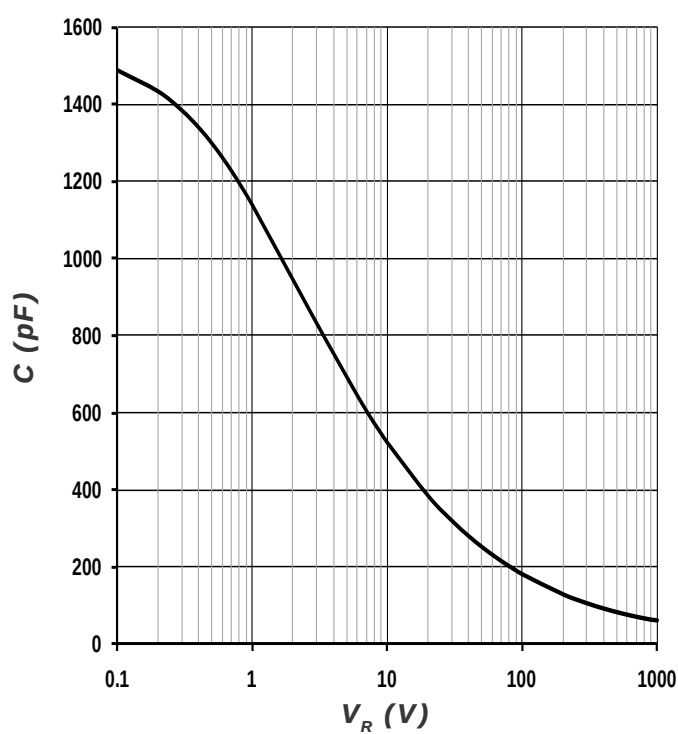


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance

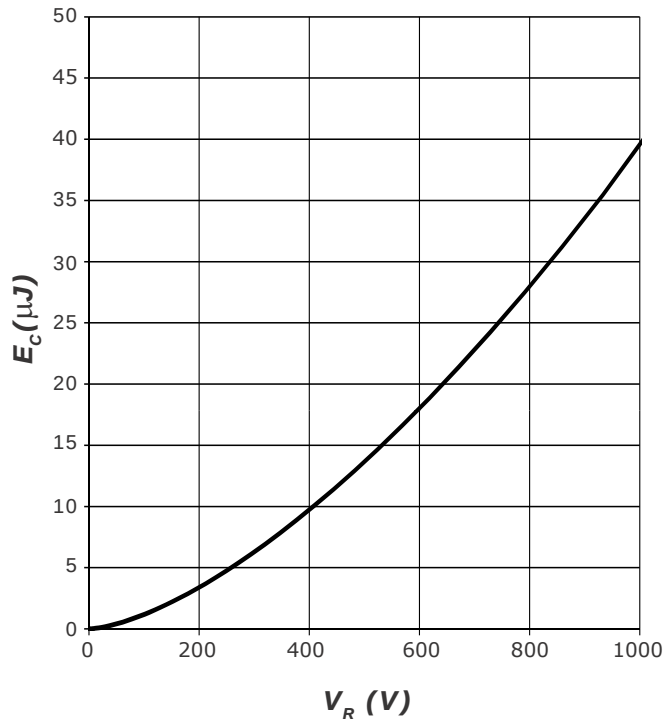


Figure 7. Typical Capacitance Stored Energy, per leg

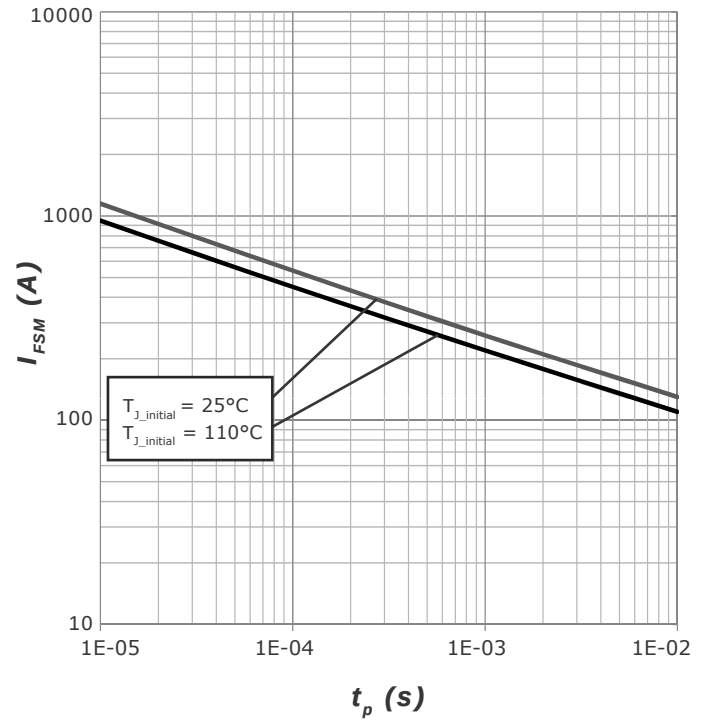


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform), per leg

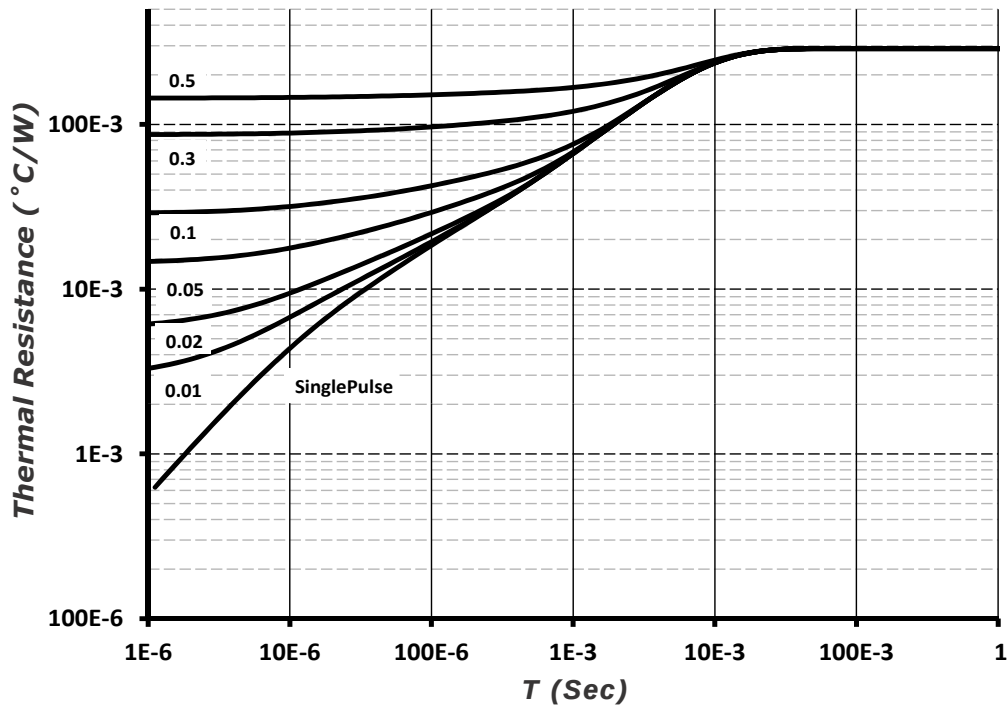
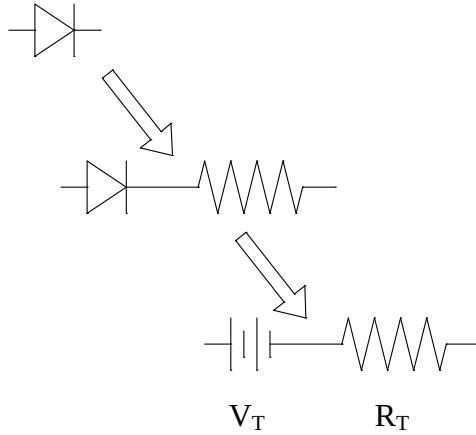


Figure 9. Device Transient Thermal Impedance



Diode Model



$$V_{FT} = V_T + I_f R_T$$

$$V_T = 0.97 + (T_J - 1.40 \times 10^{-3})$$

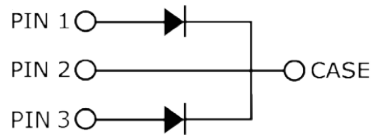
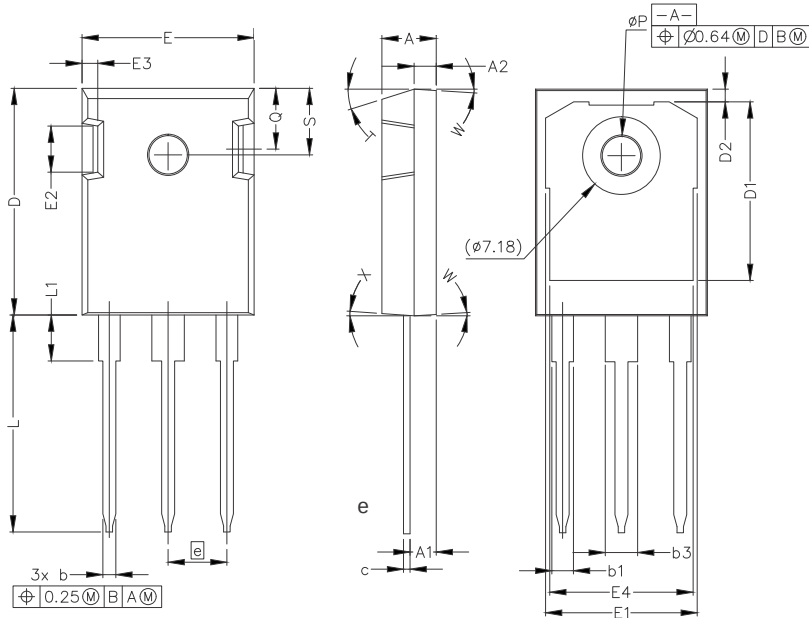
$$R_T = 0.023 + (T_J - 2.71 \times 10^{-4})$$

Note: T_J = Diode Junction Temperature In Degrees Celsius,
valid from 25°C to 175°C



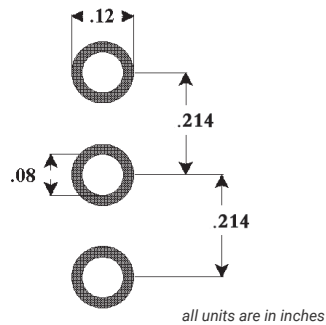
Package Dimensions

Package TO-247



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b3	.113	.133	2.87	3.38
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
N	3			
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	17.5° REF			
W	3.5° REF			
X	4° REF			

Recommended Solder Pad Layout





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